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TC 1700

Docket No.: 10191/1614

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Inventors : Richard SPITZ et al.  
Serial No. : 09/720,720  
Filed : February 28, 2001  
For : METHOD FOR ELIMINATING DEFECTS IN SILICON  
ELEMENTS THROUGH SELECTIVE ETCHING  
Examiner : TRAN, Binh  
Art Unit : 1765  
Confirmation No. : 3872

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Commissioner for Patents  
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Jong H. Lee

**RULE 116 AMENDMENT**

SIR:

This Amendment addresses the final Office Action mailed March 17, 2003, and it  
is respectfully requested that the above-identified application be amended as follows.

**In the Claims:**

Please amend claims 32 and 34 as shown below:

32. (Amended) A method for etching, comprising:

exposing a silicon element to a first heat treatment in a vacuum at a first elevated  
temperature;

selectively etching the silicon element with a gaseous etching medium and forming